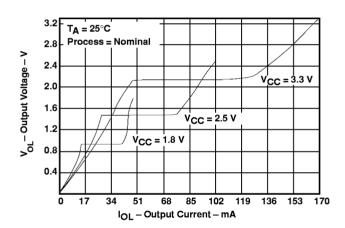
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- Member of the Texas Instruments Widebus™ Family
- EPIC[™] (Enhanced-Performance Implanted CMOS) Submicron Process
- DOC™ (Dynamic Output Control) Circuit Dynamically Changes Output Impedance, Resulting in Noise Reduction Without Speed Degradation
- Dynamic Drive Capability Is Equivalent to Standard Outputs With I_{OH} and I_{OL} of ±24 mA at 2.5-V V_{CC}

- Overvoltage-Tolerant Inputs/Outputs Allow Mixed-Voltage-Mode Data Communications
- I_{off} Feature Supports Partial Power-Down Mode Operation
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Package Options Include Plastic Thin Shrink Small-Outline (DGG) and Thin Very Small-Outline (DGV) Packages

description

A Dynamic Output Control (DOC) circuit is implemented, which, during the transition, initially lowers the output impedance to effectively drive the load and, subsequently, raises the impedance to reduce noise. Figure 1 shows typical V_{OL} vs I_{OL} and V_{OH} vs I_{OH} curves to illustrate the output impedance and drive capability of the circuit. At the beginning of the signal transition, the DOC circuit provides a maximum dynamic drive that is equivalent to a high-drive standard-output device. For more information, refer to the TI application reports, *AVC Logic Family Technology and Applications*, literature number SCEA006, and *Dynamic Output Control (DOC*TM) *Circuitry Technology and Applications*, literature number SCEA009.



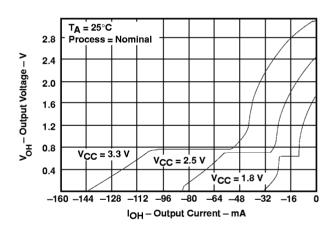


Figure 1. Output Voltage vs Output Current

This 16-bit transparent D-type latch is operational at 1.2-V to 3.6-V V_{CC} , but designed specifically for 1.65-V to 3.6-V V_{CC} operation.

The SN74AVCH16373 is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers. This device can be used as two 8-bit latches or one 16-bit latch. When the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs.



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description (continued)

A buffered output-enable (\overline{OE}) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components. \overline{OE} does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74AVCH16373 is characterized for operation from -40°C to 85°C.

terminal assignments

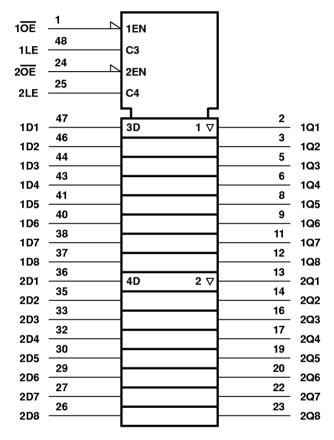
DGG OR DGV PACKAGE (TOP VIEW)					
	(10)	VIL VI	<u>'</u>		
10E	1 '	O_{48}	1LE		
1Q1	2	47] 1D1		
1Q2	3	46] 1D2		
GND	4	45	GND		
1Q3 [5	44] 1D3		
1Q4	6	43] 1D4		
V _{CC} [7	42	V _{CC}		
1Q5	8	41] 1D5		
1Q6	9	40] 1D6		
GND	10	39	GND		
1Q7	11	38	1 D7		
1Q8	12	37] 1D8		
2Q1	13	36] 2D1		
2Q2	14	35	2D2		
GND [15	34] GND		
2Q3	16	33] 2D3		
2Q4	17	32	2D4		
V _{CC} [18	31] v _{cc}		
2Q5	19	30	2D5		
2Q6	20	29] 2D6		
GND [21	28] GND		
2Q7	22	27] 2D7		
2Q8	23	26	2D8		
20E	24	25] 2LE		



FUNCTION TABLE (each 8-bit section)

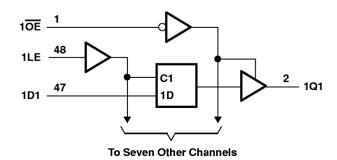
	INPUTS	ОИТРИТ	
Œ	LE	D	Q
L	Н	Н	Н
L	Н	L	L
L	L	Χ	Q_0
Н	X	Χ	Z

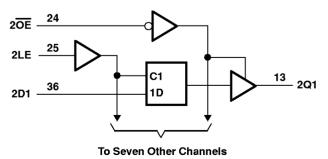
logic symbol†



[†]This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)







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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	
Input voltage range, V _I (see Note 1)	
Voltage range applied to any output in the high-impedance or power-off state, VO	
(see Note 1)	
Voltage range applied to any output in the high or low state, V _O	
(see Notes 1 and 2)	–0.5 V to V _{CC} + 0.5 V
Input clamp current, $I_{ K }(V_{ } < 0)$	
Output clamp current, I _{OK} (V _O < 0)	
Continuous output current, IO	±50 mA
Continuous current through each V _{CC} or GND	±100 mA
Package thermal impedance, θ _{JA} (see Note 3): DGG package	89°C/W
DGV package	93°C/W
Storage temperature range, T _{stg}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

- 2. The output positive-voltage rating may be exceeded up to 4.6 V maximum if the output current rating is observed.
- 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
V	Supply voltage	Operating	1.65	3.6	v	
vcc	Supply vollage	Data retention only	1.2		'	
		V _{CC} = 1.2 V	Vcc			
	High-level input voltage	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	0.65 × V _{CC}		_v	
V_{IH}	VIH High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7			
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	2			
		V _{CC} = 1.2 V		GND		
V _{IL} Low-level input voltage	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		$0.35 \times V_{CC}$	_v		
	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V	
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		8.0		
VI	Input voltage		0	3.6	V	
V-	Output voltage	Active state	0	VCC	٧	
v _O	Output voltage	3-state	0	3.6	V	
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-4		
lohs	Static high-level output current‡	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-8	mA	
		V _{CC} = 3 V to 3.6 V		-12		
I _{OLS} Static low-level output curr		V _{CC} = 1.65 V to 1.95 V		4		
	Static low-level output current‡	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		8	mA	
		V _{CC} = 3 V to 3.6 V		12		
Δt/Δν	Input transition rise or fall rate	V _{CC} = 1.65 V to 3.6 V		5	ns/V	
T_A	Operating free-air temperature		-40	85	°C	

[‡] Dynamic drive capability is equivalent to standard outputs with I_{OH} and I_{OL} of ±24 mA at 2.5-V V_{CC}. See Figure 1 for V_{OL} vs I_{OL} and V_{OH} vs I_{OH} characteristics. Refer to the TI application reports, *AVC Logic Family Technology and Applications*, literature number **SCEA006**, and *Dynamic Output Control (DOC™) Circuitry Technology and Applications*, literature number **SCEA009**.

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

F	PARAMETER	TEST CONDITIONS	Vcc	MIN	TYP	MAX	UNIT	
		I _{OHS} = -100 μA	1.65 V to 3.6 V	V _{CC} -0.	.2			
V		$I_{OHS} = -4 \text{ mA}, \qquad V_{IH} = 1.07 \text{ V}$	1.65 V	1.2			V	
VOH		$I_{OHS} = -8 \text{ mA}, \qquad V_{IH} = 1.7 \text{ V}$	2.3 V	1.75			V	
		$I_{OHS} = -12 \text{ mA}, \qquad V_{IH} = 2 \text{ V}$	3 V	2.3				
		I _{OLS} = 100 μA	1.65 V to 3.6 V			0.2		
l vai		$I_{OLS} = 4 \text{ mA}, \qquad V_{IL} = 0.57 \text{ V}$	1.65 V			0.45	٧	
VOL		$I_{OLS} = 8 \text{ mA},$ $V_{IL} = 0.7 \text{ V}$	2.3 V			0.55	V	
		$I_{OLS} = 12 \text{ mA}, \qquad V_{IL} = 0.8 \text{ V}$	3 V			0.7		
П	Control inputs	V _I = V _{CC} or GND	3.6 V			±2.5	μΑ	
		V _I = 0.57 V	1.65 V	25				
I _{BHL} ‡		$V_{I} = 0.7 V$	2.3 V	45			μΑ	
		V _I = 0.8 V	3 V	75				
		V _I = 1.07 V	1.65 V	-25				
I _{BHH} §		V _I = 1.7 V	2.3 V	-45			μΑ	
		V _I = 2 V	3 V	-75				
			1.95 V	200				
IBHLO		$V_I = 0$ to V_{CC}	2.7 V	300			μΑ	
			3.6 V	500				
			1.95 V	-200				
¹ внно [#]	ŧ	$V_I = 0$ to V_{CC}	2.7 V	-300			μΑ	
			3.6 V	-500				
loff		V _I = 0 or 3.6 V	0			±10	μΑ	
loz		V _O = V _{CC} or GND	3.6 V			±10	μΑ	
Icc		$V_I = V_{CC}$ or GND, $I_O = 0$	3.6 V			40	μΑ	
Control inner st-			2.5 V					
] _{C.}	Control inputs	V. Vocar CND	3.3 V				~E	
C _i	Data innuta	V _I = V _{CC} or GND	2.5 V				pF	
	Data inputs		3.3 V					
	Outroite	V- V or CND	2.5 V					
Co	Outputs	$V_O = V_{CC}$ or GND	3.3 V				pF	

[†] Typical values are measured at $T_A = 25$ °C.

[‡]The bus-hold circuit can sink at least the minimum low sustaining current at V_{IL} max. I_{BHL} should be measured after lowering V_{IN} to GND and then raising it to V_{IL} max.

[§] The bus-hold circuit can source at least the minimum high sustaining current at V_{IH} min. I_{BHH} should be measured after raising V_{IN} to V_{CC} and then lowering it to V_{IH} min.

[¶] An external driver must source at least IBHLO to switch this node from low to high.

[#] An external driver must sink at least I_{BHHO} to switch this node from high to low.

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timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 2 through 6)

		V _{CC} =	1.2 V	V _{CC} =	1.5 V 1 V	V _{CC} = ± 0.1		V _{CC} =		V _{CC} = ± 0.3		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _W	Pulse duration, LE high or low											ns
t _{su}	Setup time, data before LE↓											ns
th	Hold time, data after LE \downarrow											ns

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 2 through 6)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.2 V		V _{CC} = 1.2 V		$V_{CC} = 1.2 \text{ V}$ $V_{CC} = \pm 0.$		V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
	(IIVFO1)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX			
	D	Q											no		
^t pd	LE												ns		
t _{en}	ŌĒ	Q											ns		
^t dis	ŌĒ	Q										·	ns		

operating characteristics, T_A = 25°C

	PARAMETER		TEST CONDITIONS	V _{CC} = 1.8 V TYP	V _{CC} = 2.5 V TYP	V _{CC} = 3.3 V TYP	UNIT
	Power dissipation	Outputs enabled	C ₁ = 0. f = 10 MHz				pF
C _{pd}	capacitance	Outputs disabled	$C_{L} = 0, T = 10 \text{ Wiriz}$				pΓ



PRODUCT PREVIEW

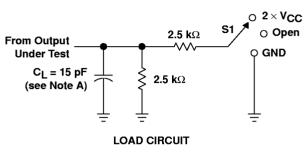
V_CC

0 V

V_{CC}/2

PARAMETER MEASUREMENT INFORMATION V_{CC} = 1.2 V

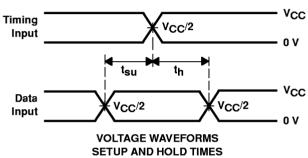
Input

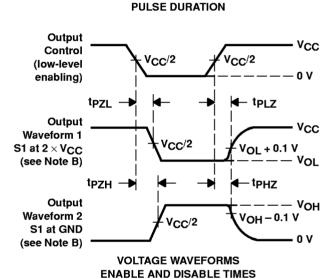


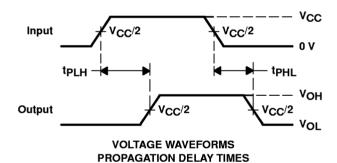
TEST	S1
t _{pd}	Open
t _{PLZ} /t _{PZL}	2×V _{CC}
tPHZ/tPZH	GND

V_{CC}/2

VOLTAGE WAVEFORMS







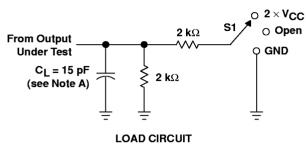
NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq$ 2 ns, $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpl 7 and tpH7 are the same as t_{dis}.
- F. tpzL and tpzH are the same as ten.
- G. tplH and tpHL are the same as tod.

Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.5 V \pm 0.1 V$

Input

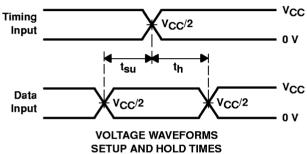


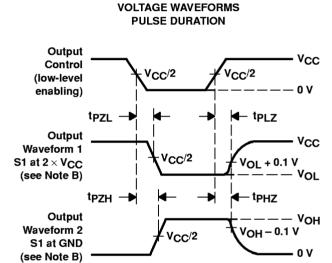
TEST	S1
^t pd	Open
t _{PLZ} /t _{PZL}	2×V _{CC}
t _{PHZ} /t _{PZH}	GND

Vcc

nν

V_{CC}/2

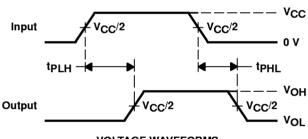




VOLTAGE WAVEFORMS

ENABLE AND DISABLE TIMES

V_{CC}/2



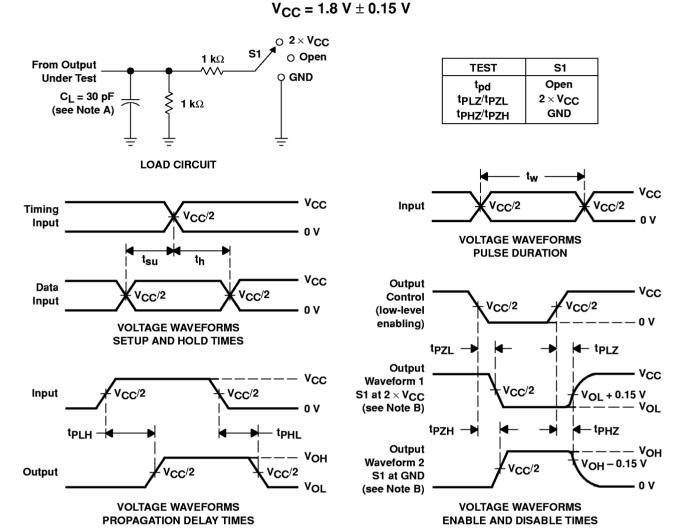
VOLTAGE WAVEFORMS PROPAGATION DELAY TIMES

- NOTES: A. C_I includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq$ 2 ns, $t_f \leq$ 2 ns.
 - The outputs are measured one at a time with one transition per measurement.
 - tpLZ and tpHZ are the same as tdis.
 - F. tp7| and tp7H are the same as ten-
 - G. tplH and tpHL are the same as tod.

Figure 3. Load Circuit and Voltage Waveforms



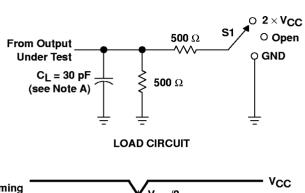
PARAMETER MEASUREMENT INFORMATION

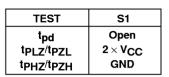


- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \Omega$, $t_r \leq$ 2 ns, $t_f \leq$ 2 ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpl 7 and tpHZ are the same as tdis.
 - F. tpzL and tpzH are the same as ten.
 - G. tpLH and tpHL are the same as tpd.

Figure 4. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$





V_{CC}/2

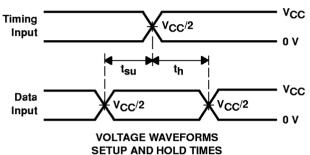
VOLTAGE WAVEFORMS

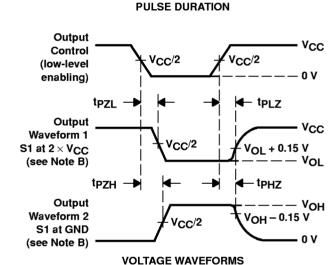
Input

V_{CC}

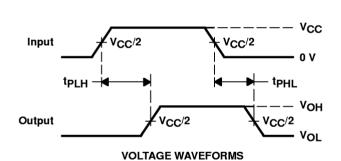
0 V

V_{CC}/2





ENABLE AND DISABLE TIMES



PROPAGATION DELAY TIMES

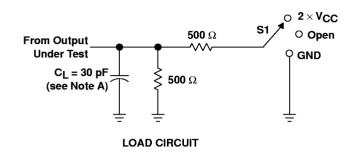
NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \ \Omega$, $t_f \leq$ 2 ns. $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tplH and tpHL are the same as tpd.

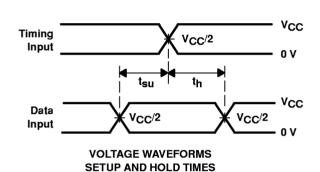
Figure 5. Load Circuit and Voltage Waveforms

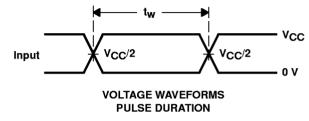
PRODUCT PREVIEW

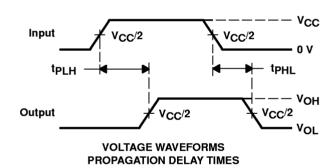
PARAMETER MEASUREMENT INFORMATION $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$

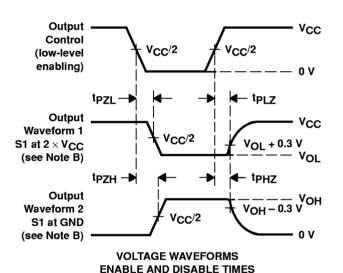


S1
Open 2 × V _{CC} GND









NOTES: A. C_I includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \ \Omega$, $t_f \leq$ 2 ns. $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpl 7 and tpH7 are the same as tdis.
- F. tp_{ZL} and tp_{ZH} are the same as t_{en} .
- G. tpLH and tpHL are the same as tpd.

Figure 6. Load Circuit and Voltage Waveforms

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